

PRODUCT FEATURES

- ☐ IGBT CHIP(Trench+FS)
- ☐ Low saturation voltage and positive temperature coefficient
- ☐ Fast switching and short tail current
- ☐ Free wheeling diodes with fast and soft reverse recovery
- ☐ Temperature sense included

APPLICATIONS

- ☐ AC motor control
- ☐ Motion/servo control
- ☐ Inverter and power supplies
- ☐ Photovoltaic/Fuel cell



IGBT-ABSOLUTE MAXIMUM RATINGS($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J=25^{\circ}\text{C}$	1200	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C=25^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	910	A
		$T_C=100^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	600	
I_{CM}	Repetitive Peak Collector Current	$tp=1\text{ms}$	1200	
P_{tot}	Power Dissipation Per IGBT	$T_C=25^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	2941	W

Diode-ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^{\circ}\text{C}$	1200	V
$I_{F(AV)}$	Average Forward Current	$T_C=80^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	600	A
I_{FRM}	Repetitive Peak Forward Current	$tp=1\text{ms}$	1200	
I^2t		$T_J=150^{\circ}\text{C}, t=10\text{ms}, V_R=0\text{V}$	100	kA^2s

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MMG600WB120B6T6 W11

IGBT-inverter

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit	
V _{GE(th)}	Gate Emitter Threshold Voltage	V _{CE} =V _{GE} , I _C =9mA	5.0	5.7	6.4	V	
V _{CE(sat)}	Collector Emitter Saturation Voltage	I _C =600A, V _{GE} =15V, T _J =25℃		1.7	2.1		
		I _C =600A, V _{GE} =15V, T _J =125℃		1.9			
		I _C =600A, V _{GE} =15V, T _J =150℃		1.95			
I _{CES}	Collector Leakage Current	V _{CE} =1200V, V _{GE} =0V, T _J =25℃			1	mA	
		V _{CE} =1200V, V _{GE} =0V, T _J =150℃			10		
I _{GES}	Gate Leakage Current	V _{CE} =0V,V _{GE} =±20V, T _J =25℃	-400		400	nA	
R _{Gint}	Integrated Gate Resistor			0.4		Ω	
Q _g	Gate Charge	V _{CE} =600V, I _C =600A , V _{GE} =15V		3.1		μC	
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f =100kHz		120		nF	
C _{oes}	Output Capacitance			4.25		nF	
C _{res}	Reverse Transfer Capacitance			600		pF	
t _{d(on)}	Turn on Delay Time	V _{CC} =600V,I _C =600A R _G =1.5Ω, V _{GE} =±15V, Inductive Load	T _J =25℃	117		ns	
			T _J =125℃	125		ns	
			T _J =150℃	135		ns	
t _r	Rise Time		T _J =25℃	73		ns	
			T _J =125℃	82		ns	
			T _J =150℃	84		ns	
t _{d(off)}	Turn off Delay Time		T _J =25℃	480		ns	
			T _J =125℃	500		ns	
			T _J =150℃	510		ns	
t _f	Fall Time	T _J =25℃	280		ns		
		T _J =125℃	400		ns		
		T _J =150℃	440		ns		
E _{on}	Turn on Energy	V _{CC} =600V,I _C =600A R _G =1.5Ω, V _{GE} =±15V, Inductive Load	T _J =25℃	23		mJ	
			T _J =125℃	41.2		mJ	
			T _J =150℃	46		mJ	
E _{off}	Turn off Energy		T _J =25℃	70.8		mJ	
			T _J =125℃	96		mJ	
			T _J =150℃	97.3		mJ	
I _{SC}	Short Circuit Current		tpsc≤10μs , V _{GE} =15V T _J =150℃ ,V _{CC} =800V		3200		A
R _{thJC}	Junction to Case Thermal Resistance （ Per IGBT ）				0.051	K /W	

MMG600WB120B6T6 W11

Diode-inverter

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V _F	Forward Voltage	I _F =600A , V _{GE} =0V, T _J =25℃		1.63	2.3	V
		I _F =600A , V _{GE} =0V, T _J =125℃		1.65		
		I _F =600A , V _{GE} =0V, T _J =150℃		1.65		
t _{rr}	Reverse Recovery Time	I _F =600A , V _R =600V dI _F /dt=-6300A/μs T _J =150℃		963		ns
I _{RRM}	Max. Reverse Recovery Current			411		A
Q _{RR}	Reverse Recovery Charge			146		μC
E _{rec}	Reverse Recovery Energy			63.4		mJ
R _{thJCD}	Junction to Case Thermal Resistance （ Per Diode ）				0.072	K /W

NTC CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
R_{25}	Resistance	$T_C=25^{\circ}\text{C}$		5		k Ω
$B_{25/50}$	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298.15 \text{ K}))]$			3375		K

MODULE CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		175	$^{\circ}\text{C}$
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
CTI	Comparative Tracking Index		> 225	
Torque	to heatsink	Recommended (M5)	2.5~5	Nm
	to terminal	Recommended (M6)	3~5	Nm
Weight			350	g

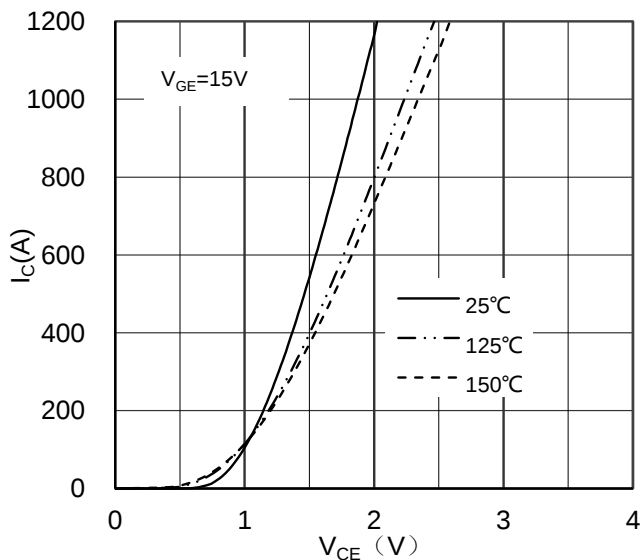


Figure 1. Typical Output Characteristics IGBT

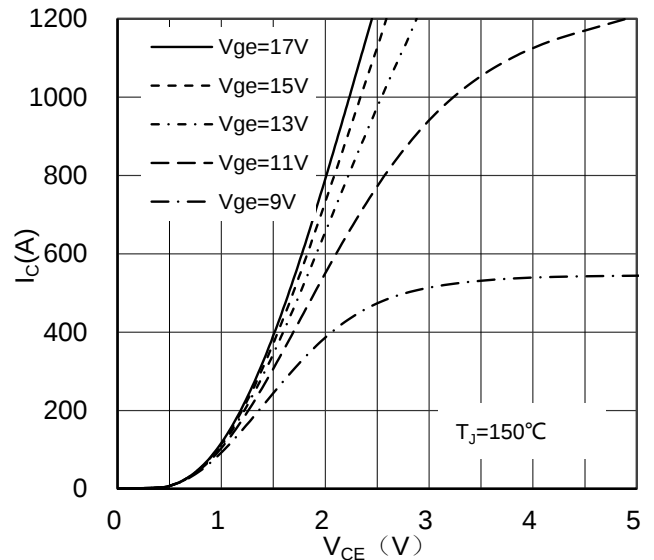


Figure 2. Typical Output Characteristics IGBT

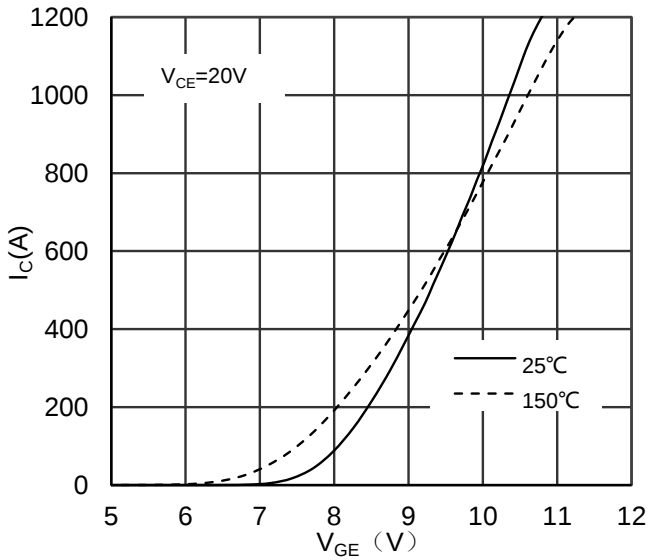


Figure 3. Typical Transfer characteristics IGBT

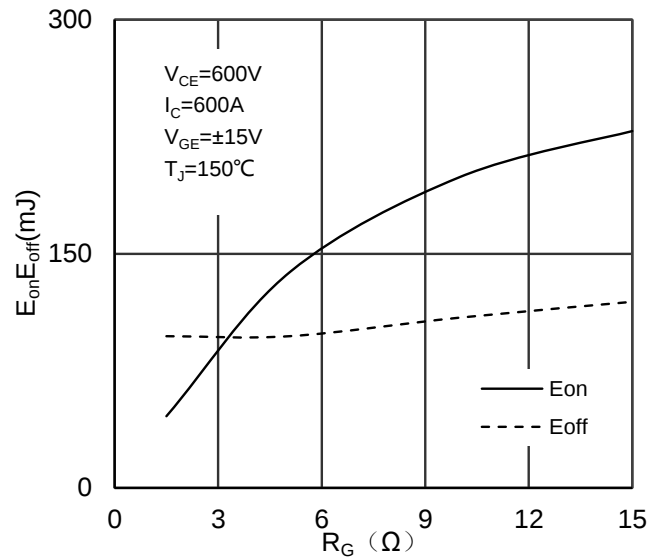


Figure 4. Switching Energy vs Gate Resistor IGBT

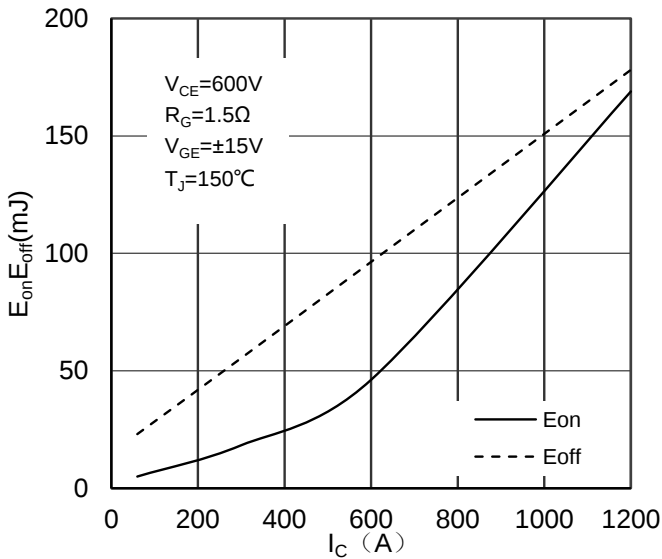


Figure 5. Switching Energy vs Collector Current IGBT

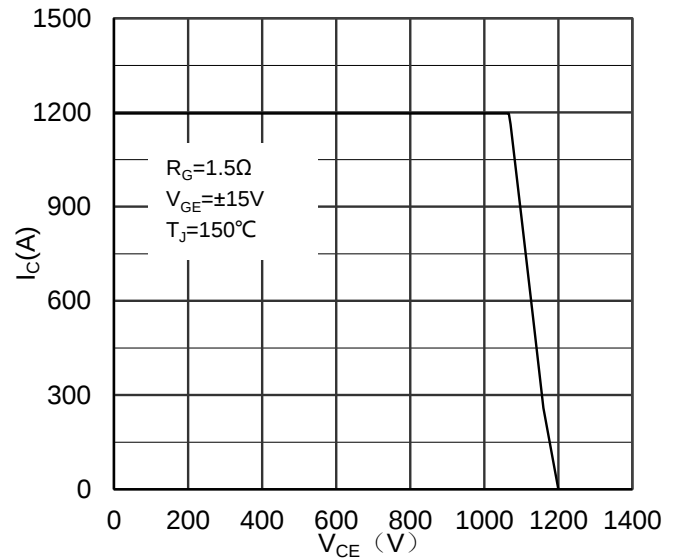


Figure 6. Reverse Biased Safe Operating Area IGBT

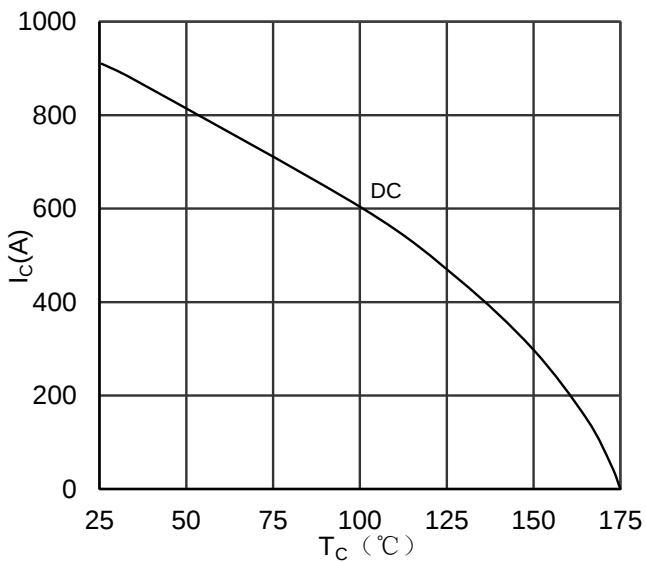


Figure 7. Collector Current vs Case temperature IGBT

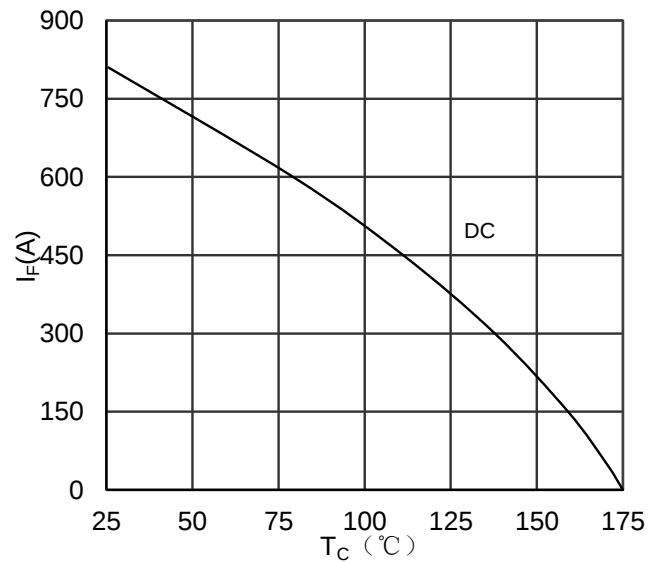


Figure 8. Forward current vs Case temperature Diode

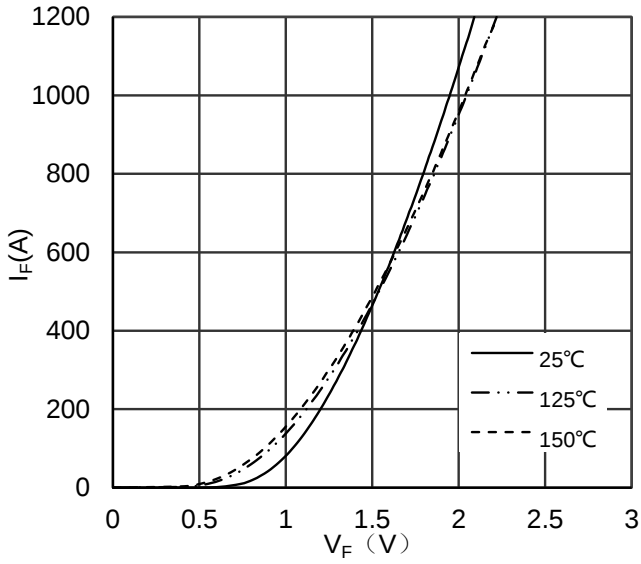


Figure 9. Diode Forward Characteristics Diode

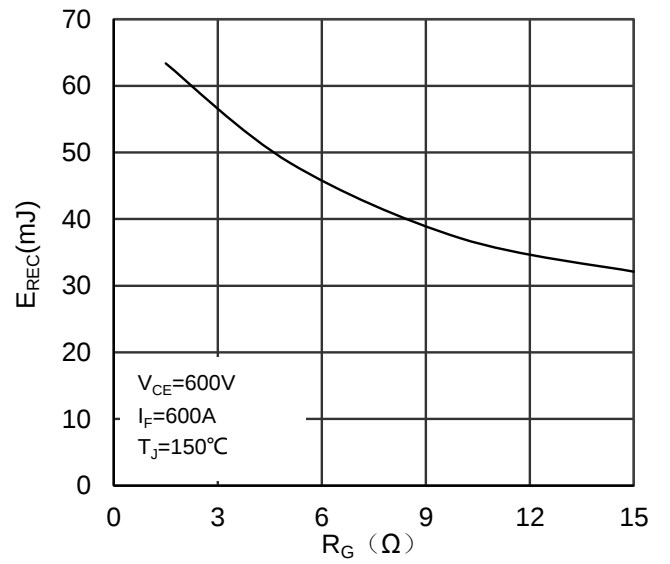


Figure 10. Switching Energy vs Gate Resistor Diode

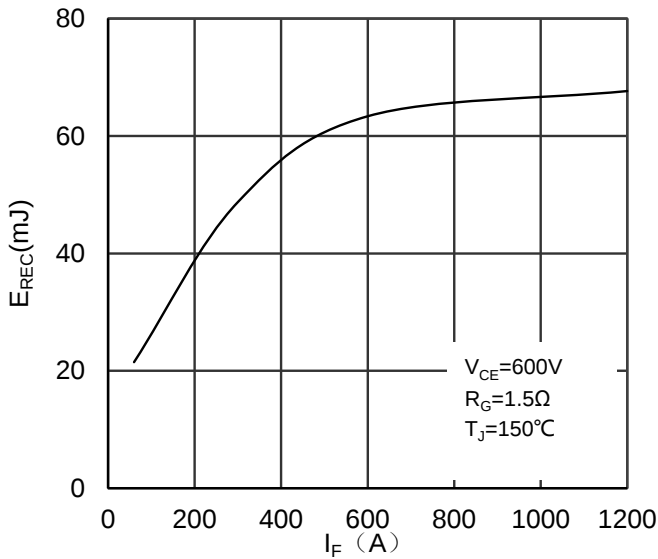


Figure 11. Switching Energy vs Forward Current Diode

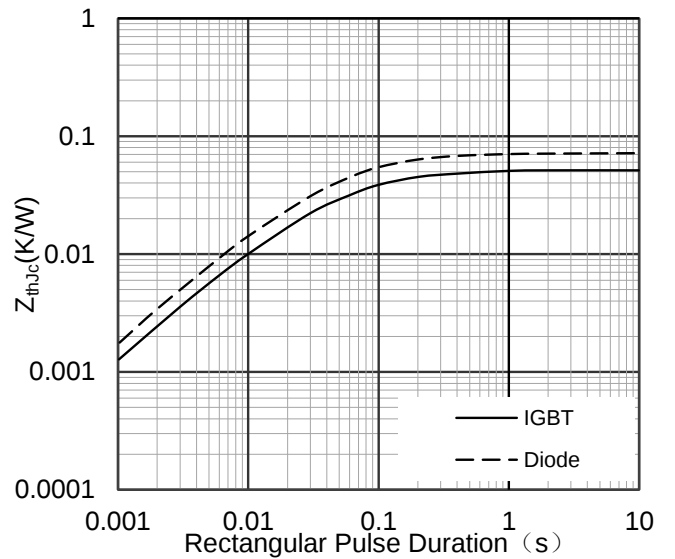


Figure 12. Transient Thermal Impedance of Diode and IGBT

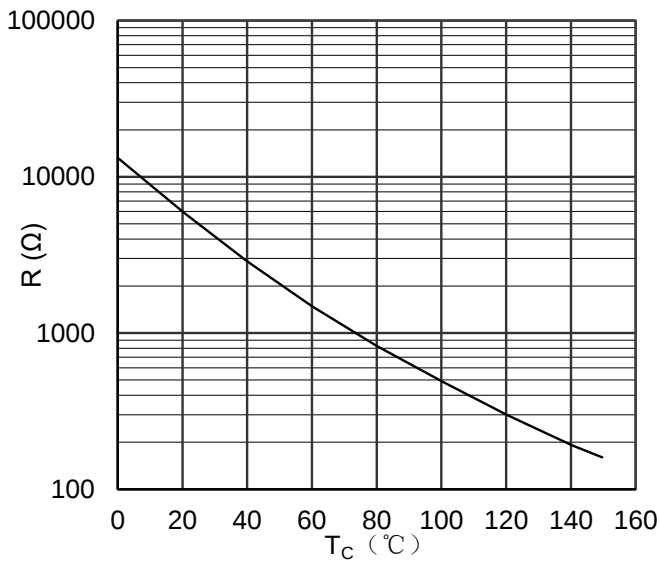


Figure 13. NTC Characteristics

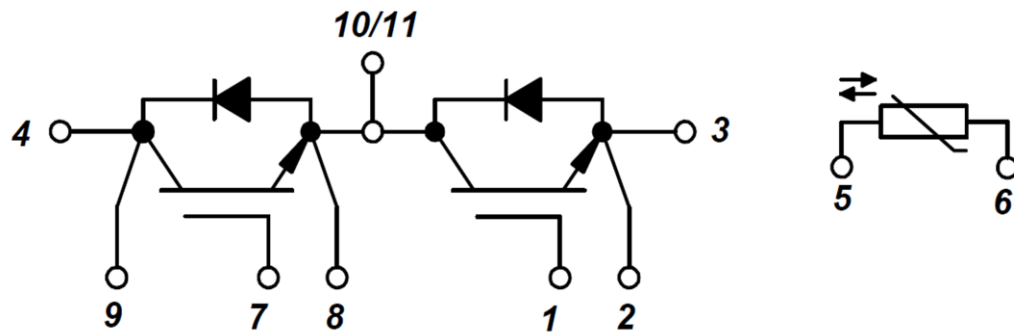
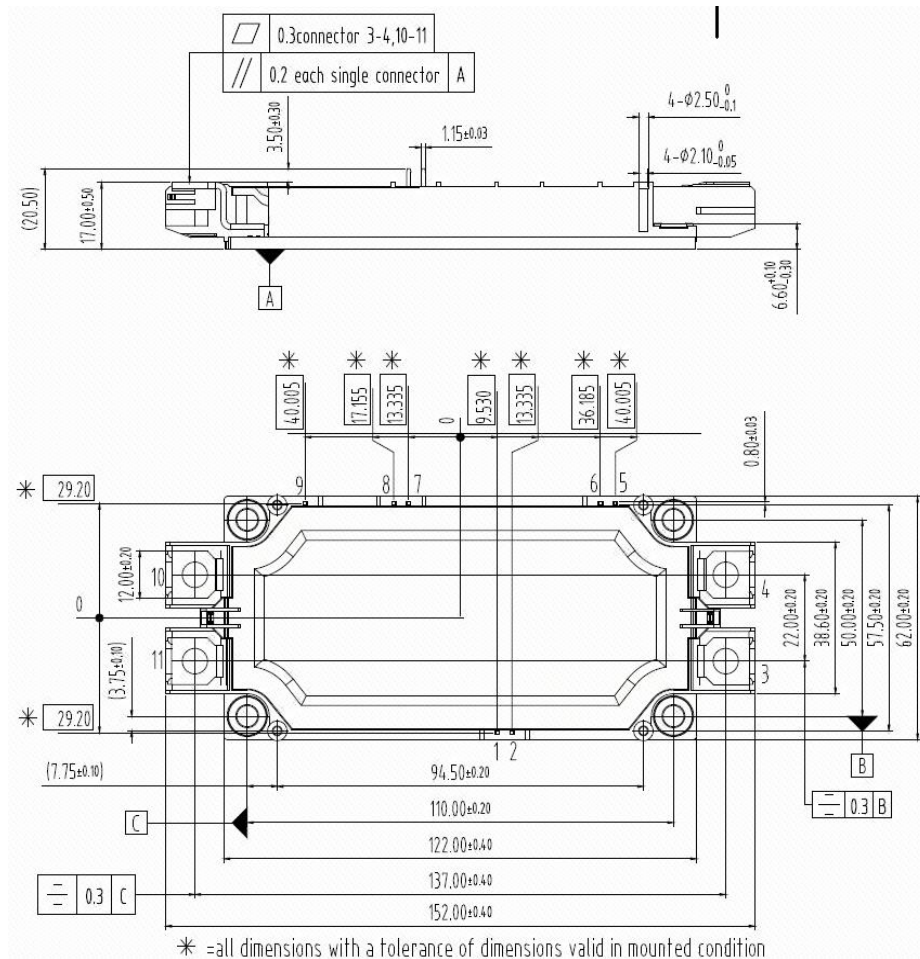


Figure 14. Circuit Diagram



Dimensions in (mm)

Figure 15. Package Outline